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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: : Date: February 11, 1998
Matthias Passlack et al. :

Docket No.: GE04270 ✓ :

Filed: Concurrently Herewith :

For: SELF-ALIGNED METAL-OXIDE-COMPOUND
SEMICONDUCTOR DEVICE AND METHOD
OF FABRICATION :

DISCLOSURE STATEMENT UNDER 37 CFR 1.56

Honorable Commissioner of Patents and Trademarks,
Washington, D.C. 20231

SIR:

It is respectfully requested that the art listed below be considered in the examination of the subject application and made of record therein. A copy of the below listed art is enclosed herewith.

No representation is made or intended that a search has been made or that no better art than listed is available.

Citations


1. U.S. Patent 5,124,762, T. Childs et al., "GAAS Heterostructure Metal-Insulator-Semiconductor Integrated Circuit Technology", (June 23, 1992).
2. U.S. Patent 5,451,548, N.E. Hunt et al., "Electron Beam Deposition of Gallium Oxide Thin Films Using a Single High Purity Crystal Source", (September 19, 1995).
3. U.S. Patent 5,550,089, N. K. Dutta et al., "Gallium Oxide Coatings for Optoelectronic Devices Using Electron Beam Evaporation of a High Purity Single Crystal $\text{GD}_3\text{GA}_5\text{O}_{12}$ Source", (August 27, 1996).

4. U.S. Patent 5,665,658, M. Passlack , "Method of Forming a Dielectric Layer Structure", (September 9, 1997).
5. U.S. Patent 5,597,768, M. Passlack, "Method of Forming a Ga_2O_3 Dielectric Layer", (January 28, 1997).
6. An article entitled "Thermodynamic and photochemical stability of low interface state density Ga_2O_3 -GaAs structures fabricated by in situ molecular beam epitaxy" from Appl. Phys. Lett. 69(3) , M. Passlack et al., pages 302-304 (July 15, 1996).
7. An article entitled "Recombination velocity at oxide-GaAs interfaces fabricated by in situ molecular beam epitaxy" from Appl. Phys. Lett. 68(25), M. Passlack et al., pages 3605-3607 (June 17, 1996).
8. An article entitled "Quasistatic and high frequency capacitance-voltage characterization of Ga_2O_3 -GaAs structures fabricated by in situ molecular beam epitaxy" from Appl. Phys. Lett. Volume 68, No. 8, M. Passlack et al., pages 1099-1101 (February 19, 1996).
9. An article entitled "Anisotropy of electrical and optical properties in B- Ga_2O_3 single crystals" from Appl. Phys. Lett. 71(7), N. Ueda et al., pages 933-935 (August 18, 1997).
10. An article entitled "Synthesis and control of conductivity of ultraviolet transmitting B- Ga_2O_3 single crystals" from Appl. Phys. Lett. 70(26), N. Ueda, pages 3561-3563 (June 30, 1997).

Respectfully submitted,

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